

Tae-Youb Kim

List of Publications by Year in descending order

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33
times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Highly efficient hybrid light-emitting transistors incorporating MoO ₃ /Ag/MoO ₃ semi-transparent electrodes. Journal of Materials Chemistry C, 2022, 10, 880-885.	5.5	3
2	Long-lived electrochromic device with multilevel bistability based on portable film-type polymer electrolytes. Solar Energy Materials and Solar Cells, 2021, 221, 110883.	6.2	9
3	Bistable mirror/transparent reversibly electrodeposited devices with TiO ₂ as the mediator. Solar Energy Materials and Solar Cells, 2020, 206, 110343.	6.2	10
4	Reflective-Type Transparent/Colored Mirror Switchable Device Using Reversible Electrodeposition with Fabry-Perot Interferometer. Advanced Materials Technologies, 2020, 5, 2000367.	5.8	10
5	Switchable Holographic Device Based on Reversible Electrodeposition. Advanced Materials Technologies, 2019, 4, 1800478.	5.8	3
6	Graphene Electrode Enabling Electrochromic Approaches for Daylight-Dimming Applications. Scientific Reports, 2018, 8, 3944.	3.3	12
7	Electrochromic device with self-diffusing function for light adaptable displays. Solar Energy Materials and Solar Cells, 2018, 177, 89-96.	6.2	7
8	New switchable mirror device with a counter electrode based on reversible electrodeposition. Solar Energy Materials and Solar Cells, 2018, 179, 161-168.	6.2	26
9	Fabrication of Highly Transparent Electrochromic Mirror Device with Nanoporous Counter Electrode. Bulletin of the Korean Chemical Society, 2018, 39, 1186-1192.	1.9	11
10	Nitrogen Doping Effect for Improving Operation Reliability of Phase Modulator Using Ge ₂ Sb ₂ Te ₅ Thin Film for Hologram Image Implementation. Journal of Nanoscience and Nanotechnology, 2018, 18, 6033-6039.	0.9	3
11	Holographic image generation with a thin-film resonance caused by chalcogenide phase-change material. Scientific Reports, 2017, 7, 41152.	3.3	54
12	Design Method of Tunable Pixel with Phase-Change Material for Diffractive Optical Elements. ETRI Journal, 2017, 39, 390-397.	2.0	8
13	Effects of Pre-reducing Sb-Doped SnO ₂ Electrodes in Viologen-Anchored TiO ₂ Nanostructure-Based Electrochromic Devices. ETRI Journal, 2016, 38, 469.	2.0	4
14	Optical and Electrical Properties of Electrochromic Devices Depending on Electrolyte Concentrations and Cell Gaps. Bulletin of the Korean Chemical Society, 2016, 37, 1812-1819.	1.9	10
15	Design and Fabrication of Integrated Fabry-Perot Type Color Reflector for Reflective Displays. Journal of Nanoscience and Nanotechnology, 2016, 16, 5038-5043.	0.9	6
16	Electrochromic mirror using viologen-anchored nanoparticles. Materials Research Bulletin, 2016, 82, 16-21.	5.2	27
17	Driving mechanism of high speed electrochromic devices by using patterned array. Solar Energy Materials and Solar Cells, 2016, 145, 76-82.	6.2	10
18	Paper No S4.4: Colored OLED With a Multilayered Graphene Electrode for Light-Adaptable Displays. Digest of Technical Papers SID International Symposium, 2015, 46, 20-20.	0.3	0

#	ARTICLE	IF	CITATIONS
19	Strong visible electroluminescence from silicon nanocrystals embedded in a silicon carbide film. Applied Physics Letters, 2015, 106, .	3.3	15
20	Electrochromic device for the reversible electrodeposition system. Journal of Information Display, 2014, 15, 13-17.	4.0	28
21	In situ-grown hexagonal silicon nanocrystals in silicon carbide-based films. Nanoscale Research Letters, 2012, 7, 634.	5.7	12
22	Comparative Study of Silicon Quantum Dot Formation In-situ Grown with a Gas Mixture of SiH ₄ +N ₂ and SiH ₄ +NH ₃ . Journal of the Korean Physical Society, 2011, 59, 308-311.	0.7	2
23	Effects of the Hole Tunneling Barrier Width on the Electrical Characteristic in Silicon Quantum Dots Light-Emitting Diodes. Japanese Journal of Applied Physics, 2011, 50, 04DG11.	1.5	1
24	Photosensitive biosensor array system using optical addressing without an addressing circuit on array biochips. Applied Physics Letters, 2010, 97, .	3.3	11
25	Modified ion sensitive field effect transistor sensors having an extended gate on a thick dielectric. Applied Physics Letters, 2010, 96, 203702.	3.3	6
26	Biosensors using the Si nanochannel junction-isolated from the Si bulk substrate. Journal of Applied Physics, 2009, 106, 114701.	2.5	4
27	Physics and Device Structures of Highly Efficient Silicon Quantum Dots Based Silicon Nitride Light-Emitting Diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1545-1555.	2.9	46
28	Effects of Ag/indium tin oxide contact to a SiC doping layer on performance of Si nanocrystal light-emitting diodes. Applied Physics Letters, 2006, 88, 131913.	3.3	13
29	Enhancement of light extraction from a silicon quantum dot light-emitting diode containing a rugged surface pattern. Applied Physics Letters, 2006, 89, 191120.	3.3	23
30	The dot size effect of amorphous silicon quantum dot on 1.54- μ m Erluminescence. Materials Research Society Symposia Proceedings, 2004, 817, 31.	0.1	2
31	Quantum confinement effect of silicon nanocrystals in situ grown in silicon nitride films. Applied Physics Letters, 2004, 85, 5355-5357.	3.3	286
32	Hydrogenation effect on 1.54- μ m Er luminescence in Er-doped amorphous silicon quantum dot films. , 0, , ,		0
33	High efficiency silicon visible light emitter using silicon nanocrystals in silicon nitride matrix and transparent doping layer. , 0, , ,		0